

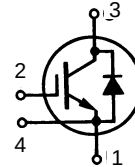
IGBT with Diode

IXSN 52N60AU1

Combi Pack

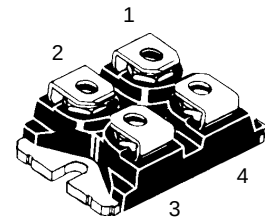
$$\begin{aligned} V_{CES} &= 600 \text{ V} \\ I_{C25} &= 80 \text{ A} \\ V_{CE(sat)} &= 3 \text{ V} \end{aligned}$$

Short Circuit SOA Capability



Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	600	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1 \text{ M}\Omega$	600	A
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	80	A
I_{C90}	$T_C = 90^\circ\text{C}$	40	A
I_{CM}	$T_C = 25^\circ\text{C}, 1 \text{ ms}$	160	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}, T_{VJ} = 125^\circ\text{C}, R_G = 22 \Omega$ Clamped inductive load, $L = 30 \mu\text{H}$	$I_{CM} = 80$ @ $0.8 V_{CES}$	A
t_{SC} (SCSOA)	$V_{GE} = 15 \text{ V}, V_{CE} = 360 \text{ V}, T_J = 125^\circ\text{C}$ $R_G = 22 \Omega$, non repetitive	10	μs
P_C	$T_C = 25^\circ\text{C}$	250	W
V_{ISOL}	50/60 Hz	$t = 1 \text{ min}$	2500 V~
	$I_{ISOL} \leq 1 \text{ mA}$	$t = 1 \text{ s}$	3000 V~
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
M_d	Mounting torque	1.5/13	Nm/lb.in.
	Terminal connection torque (M4)	1.5/13	Nm/lb.in.
Weight		30	g

miniBLOC, SOT-227 B



1 = Emitter ①, 3 = Collector
2 = Gate, 4 = Emitter ①

① Either Emitter terminal can be used as Main or Kelvin Emitter

Features

- International standard package miniBLOC
- Aluminium-nitride isolation
 - high power dissipation
- Isolation voltage 3000 V~
- Low $V_{CE(sat)}$
 - for minimum on-state conduction losses
- Fast Recovery Epitaxial Diode
 - short t_{rr} and I_{RM}
- Low collector-to-case capacitance (< 50 pF)
 - reduces RFI
- Low package inductance (< 10 nH)
 - easy to drive and to protect

Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

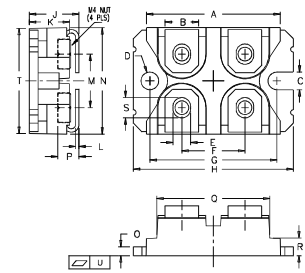
Advantages

- Space savings
- Easy to mount with 2 screws
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 3 \text{ mA}, V_{GE} = 0 \text{ V}$	600		V
$V_{GE(th)}$	$I_C = 4 \text{ mA}, V_{CE} = V_{GE}$	4		V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0 \text{ V}$	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		750 μA
				15 mA
I_{GES}	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}, V_{GE} = 15 \text{ V}$			3 V

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$I_C = I_{C90}, V_{CE} = 10\text{ V}$, Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $d \leq 2\%$	20	23	S
C_{ies}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		4500	pF
C_{oes}			400	pF
C_{res}			90	pF
Q_g	$I_C = I_{C90}, V_{GE} = 15\text{ V}$, $V_{CE} = 0.5 V_{CES}$		190	250 nC
Q_{ge}			45	60 nC
Q_{gc}			88	120 nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = I_{C90}, V_{GE} = 15\text{ V}$, $L = 100\text{ }\mu\text{H}$, $V_{CE} = 0.8 V_{CES}$, $R_G = 2.7\text{ }\Omega$ Remarks: Switching times may increase for $V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$, higher T_J or increased R_G		70	ns
t_{ri}			220	ns
$t_{d(off)}$			200	ns
t_{fi}			200	ns
E_{off}			3.5	mJ
$t_{d(on)}$			70	ns
t_{ri}	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = I_{C90}, V_{GE} = 15\text{ V}$, $L = 100\text{ }\mu\text{H}$, $V_{CE} = 0.8 V_{CES}$, $R_G = 2.7\text{ }\Omega$ Remarks: Switching times may increase for $V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$, higher T_J or increased R_G		220	ns
E_{on}			4.7	mJ
$t_{d(off)}$			450	ns
t_{fi}			340	600 ns
E_{off}			6	mJ
R_{thJC}				0.50 K/W
R_{thCK}			0.05	K/W

miniBLOC, SOT-227 B



M4 screws (4x) supplied

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	38.00	38.23	1.496	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_F	$I_F = I_{C90}, V_{GE} = 0\text{ V}$, Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $d \leq 2\%$			1.8 V
I_{RM}	$I_F = I_{C90}, V_{GE} = 0\text{ V}$, $-di_F/dt = 480\text{ A}/\mu\text{s}$ $V_R = 360\text{ V}$ $I_F = 1\text{ A}$, $-di_F/dt = 200\text{ A}/\mu\text{s}$; $V_R = 30\text{ V}$		19	A
t_{rr}			175	ns
			35	50 ns
R_{thJC}				0.80 K/W

Fig.1 Saturation Characteristics

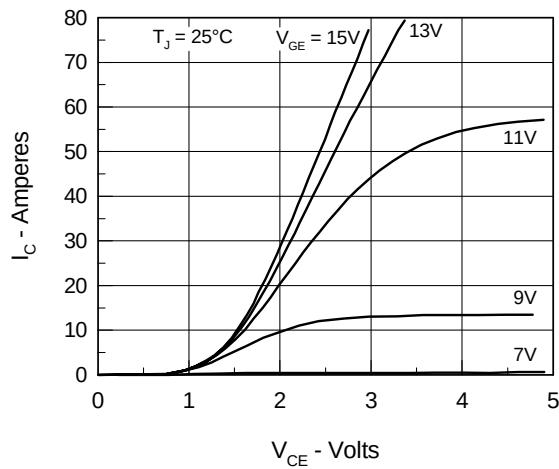


Fig.2 Output Characteristics

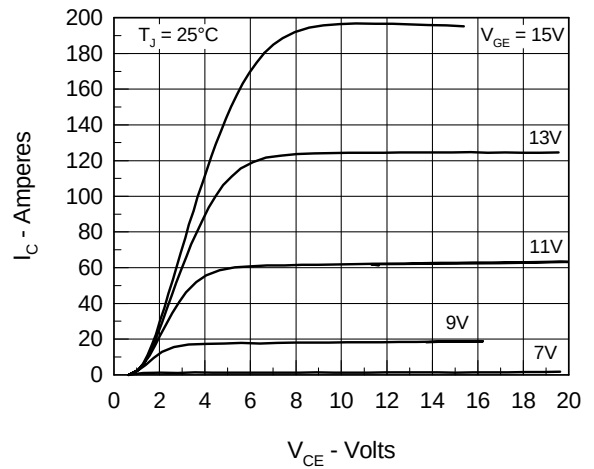


Fig.3 Collector-Emitter Voltage vs. Gate-Emitter Voltage

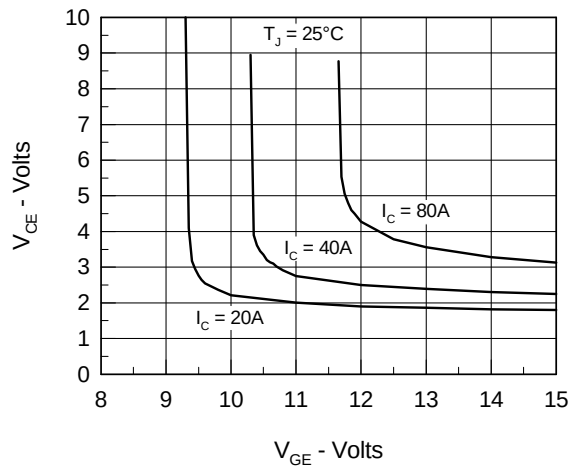


Fig.4 Temperature Dependence of Output Saturation Voltage

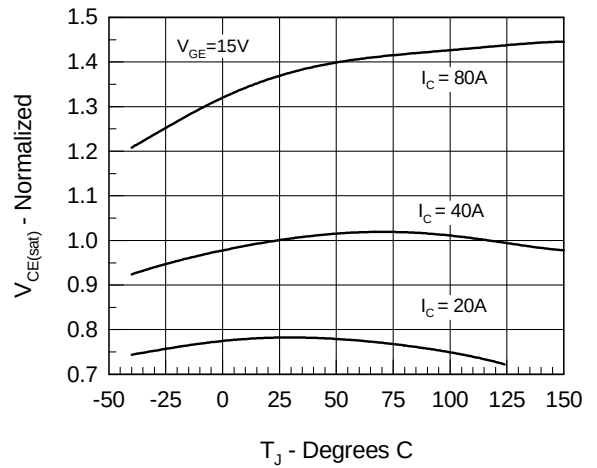


Fig.5 Input Admittance

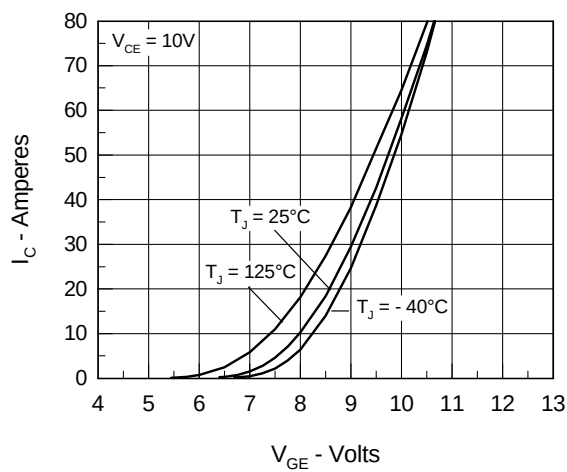


Fig.6 Temperature Dependence of Breakdown and Threshold Voltage

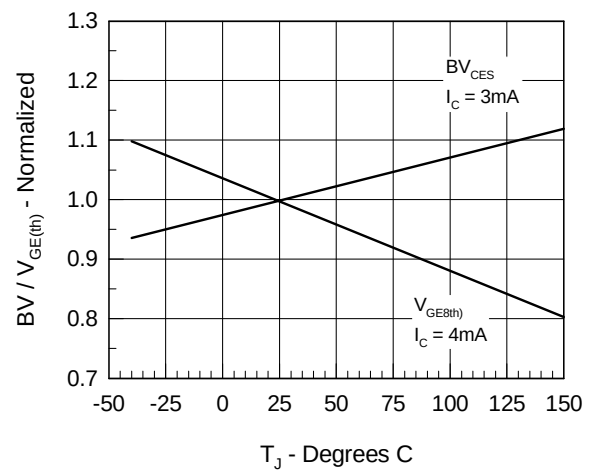


Fig.7 Turn-Off Energy per Pulse and Fall Time on Collector Current

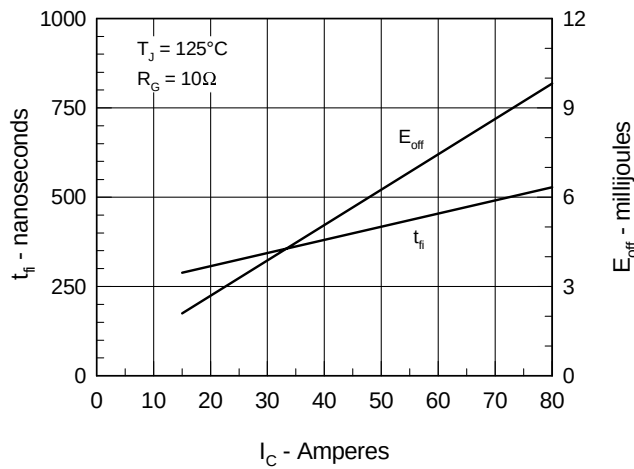


Fig.8 Dependence of Turn-Off Energy Per Pulse and Fall Time on R_G

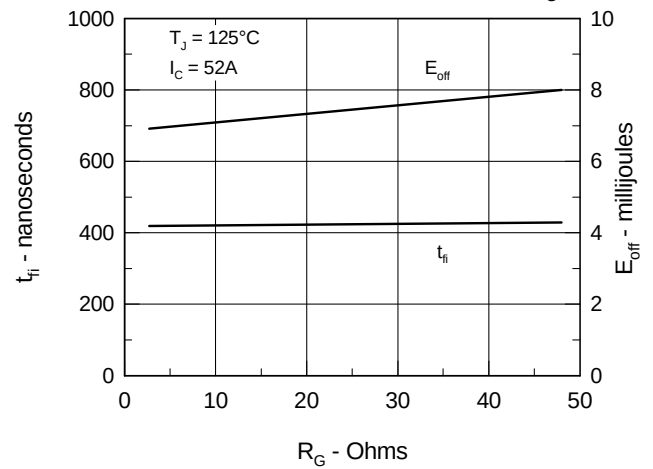


Fig.9 Gate Charge Characteristic Curve

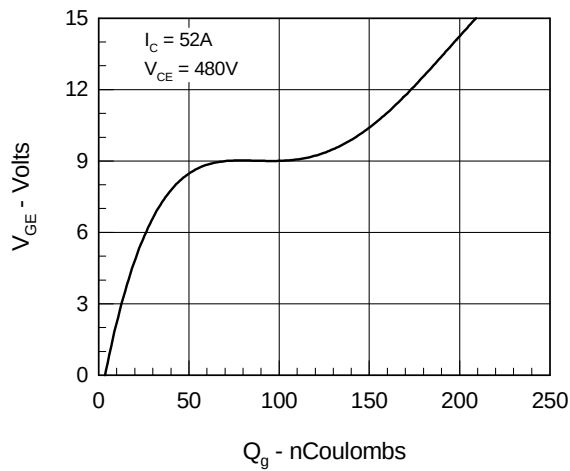


Fig.10 Turn-Off Safe Operating Area

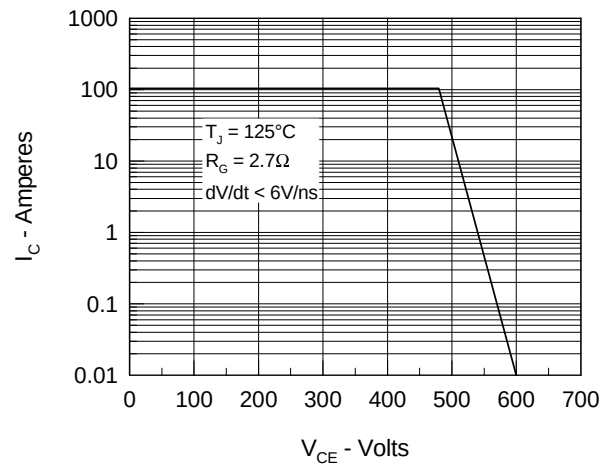
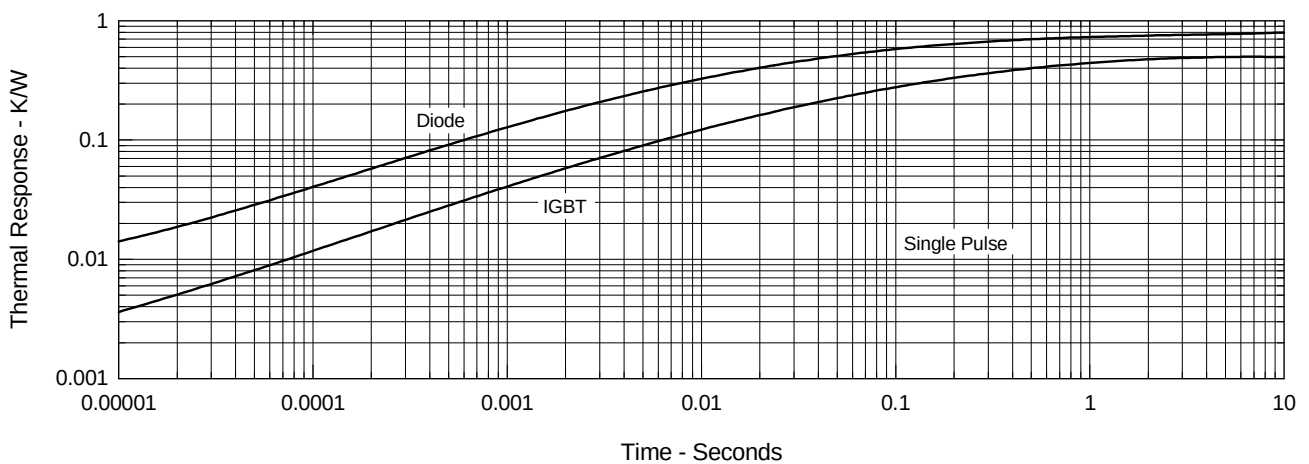


Fig.11 Transient Thermal Impedance



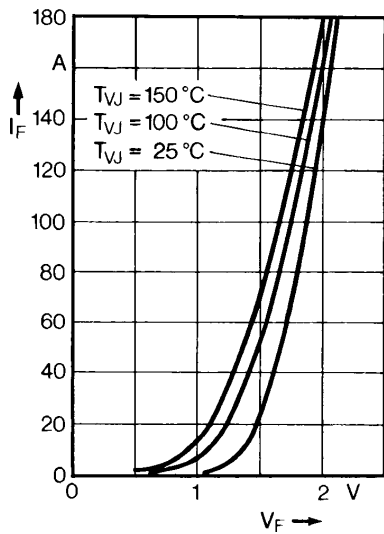


Fig. 12 Forward current versus voltage drop.

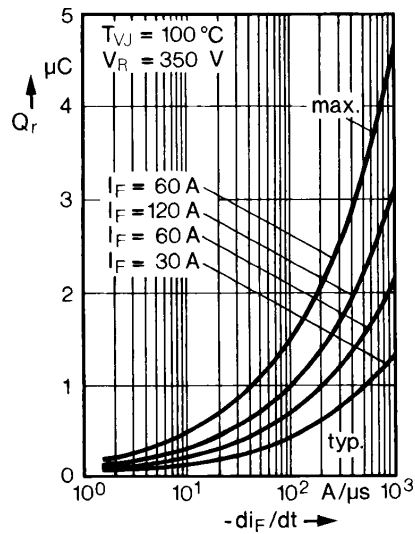


Fig. 13 Recovery charge versus $-di_F/dt$.

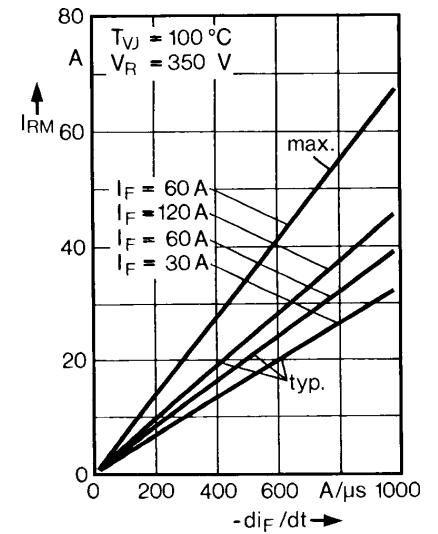


Fig. 14 Peak reverse current versus $-di_F/dt$.

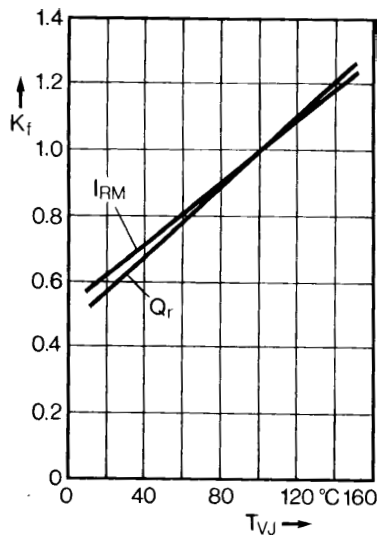


Fig. 15 Dynamic parameters versus junction temperature.

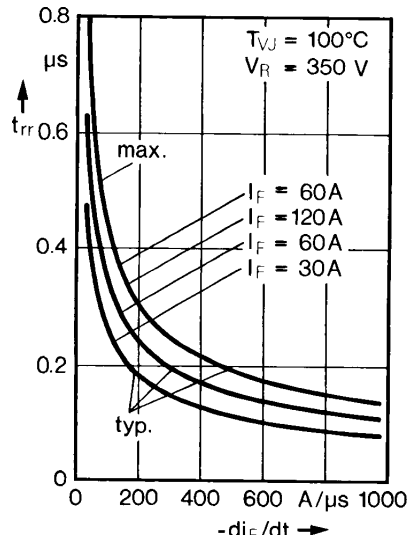


Fig. 16 Recovery time versus $-di_F/dt$.

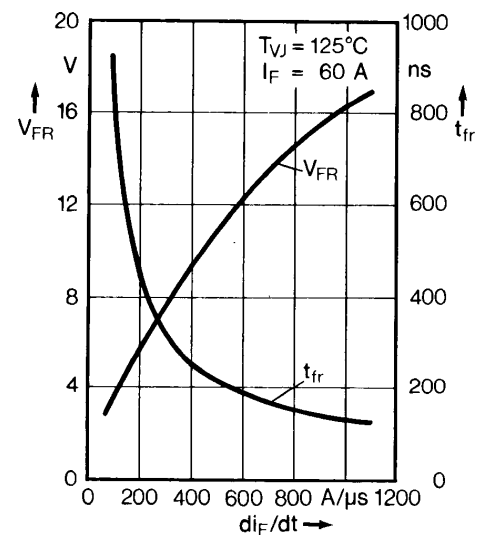


Fig. 17 Peak forward voltage vs. di_F/dt .

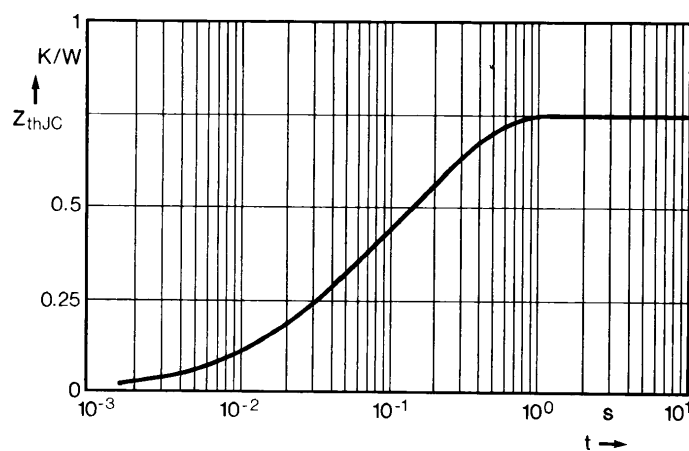


Fig. 18 Transient thermal impedance junction to case.